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# FCH085N80

## N-Channel SuperFET® II MOSFET

800 V, 46 A, 85 mΩ

April 2016

### Features

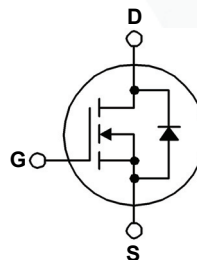
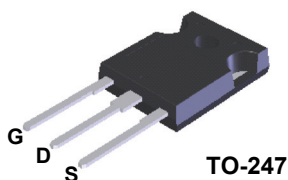
- Typ.  $R_{DS(on)}$  = 67 mΩ
- 850 V @  $T_J = 150^{\circ}\text{C}$
- Ultra Low Gate Charge (Typ.  $Q_g = 196$  nC)
- Low  $E_{OSS}$  (Typ. 18 μJ @ 400 V)
- Low Effective Output Capacitance (Typ.  $C_{OSS(eff.)} = 568$  pF)
- 100% Avalanche Tested
- RoHS Compliant

### Applications

- AC-DC Power Supply
- LED Lighting

### Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



### Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                            |                                              | FCH085N80_F155 | Unit |
|----------------|----------------------------------------------------------------------|----------------------------------------------|----------------|------|
| $V_{DSS}$      | Drain to Source Voltage                                              |                                              | 800            | V    |
| $V_{GSS}$      | Gate to Source Voltage                                               | - DC                                         | ±20            | V    |
|                |                                                                      | - AC (f > 1 Hz)                              | ±30            |      |
| $I_D$          | Drain Current                                                        | - Continuous ( $T_C = 25^{\circ}\text{C}$ )  | 46             | A    |
|                |                                                                      | - Continuous ( $T_C = 100^{\circ}\text{C}$ ) | 29             |      |
| $I_{DM}$       | Drain Current                                                        | - Pulsed (Note 1)                            | 138            | A    |
| $E_{AS}$       | Single Pulsed Avalanche Energy                                       | (Note 2)                                     | 1701           | mJ   |
| $I_{AR}$       | Avalanche Current                                                    | (Note 1)                                     | 9.2            | A    |
| $E_{AR}$       | Repetitive Avalanche Energy                                          | (Note 1)                                     | 4.4            | mJ   |
| dv/dt          | MOSFET dv/dt                                                         |                                              | 100            | V/ns |
|                | Peak Diode Recovery dv/dt                                            | (Note 3)                                     | 20             |      |
| $P_D$          | Power Dissipation                                                    | ( $T_C = 25^{\circ}\text{C}$ )               | 446            | W    |
|                |                                                                      | - Derate Above 25°C                          | 3.5            | W/°C |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                              |                                              | -55 to +150    | °C   |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds |                                              | 300            | °C   |

### Thermal Characteristics

| Symbol          | Parameter                                     | FCH085N80_F155 | Unit |
|-----------------|-----------------------------------------------|----------------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max.    | 0.28           | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 40.0           |      |

## Package Marking and Ordering Information

| Part Number    | Top Mark  | Package    | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|------------|----------------|-----------|------------|----------|
| FCH085N80_F155 | FCH085N80 | TO-247 G03 | Tube           | N/A       | N/A        | 30 units |

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

### Off Characteristics

|                                |                                           |                                                                       |     |     |           |                           |
|--------------------------------|-------------------------------------------|-----------------------------------------------------------------------|-----|-----|-----------|---------------------------|
| $BV_{DSS}$                     | Drain to Source Breakdown Voltage         | $V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$      | 800 | -   | -         | V                         |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$                | -   | 0.8 | -         | $\text{V}/^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$                          | -   | -   | 25        | $\mu\text{A}$             |
|                                |                                           | $V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$ | -   | -   | 250       |                           |
| $I_{GSS}$                      | Gate to Body Leakage Current              | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$                       | -   | -   | $\pm 100$ | nA                        |

### On Characteristics

|              |                                      |                                           |     |    |     |                  |
|--------------|--------------------------------------|-------------------------------------------|-----|----|-----|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage               | $V_{GS} = V_{DS}, I_D = 4.6\text{ mA}$    | 2.5 | -  | 4.5 | V                |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}, I_D = 23\text{ A}$ | -   | 67 | 85  | $\text{m}\Omega$ |
| $g_{FS}$     | Forward Transconductance             | $V_{DS} = 20\text{ V}, I_D = 23\text{ A}$ | -   | 55 | -   | S                |

### Dynamic Characteristics

|                 |                               |                                                                              |   |      |       |          |
|-----------------|-------------------------------|------------------------------------------------------------------------------|---|------|-------|----------|
| $C_{iss}$       | Input Capacitance             | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$               | - | 8140 | 10825 | pF       |
| $C_{oss}$       | Output Capacitance            |                                                                              | - | 255  | 340   | pF       |
| $C_{rss}$       | Reverse Transfer Capacitance  |                                                                              | - | 10   | -     | pF       |
| $C_{oss}$       | Output Capacitance            | $V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$               | - | 1000 | -     | pF       |
| $C_{oss(eff.)}$ | Effective Output Capacitance  | $V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$                  | - | 728  | -     | pF       |
| $Q_{g(tot)}$    | Total Gate Charge at 10V      | $V_{DS} = 640\text{ V}, I_D = 46\text{ A}, V_{GS} = 10\text{ V}$<br>(Note 4) | - | 196  | 255   | nC       |
| $Q_{gs}$        | Gate to Source Gate Charge    |                                                                              | - | 40   | -     | nC       |
| $Q_{gd}$        | Gate to Drain "Miller" Charge |                                                                              | - | 72   | -     | nC       |
| ESR             | Equivalent Series Resistance  | $f = 1\text{ MHz}$                                                           | - | 0.8  | -     | $\Omega$ |

### Switching Characteristics

|              |                     |                                                                                                       |   |     |     |    |
|--------------|---------------------|-------------------------------------------------------------------------------------------------------|---|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 400\text{ V}, I_D = 46\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$<br>(Note 4) | - | 45  | 100 | ns |
| $t_r$        | Turn-On Rise Time   |                                                                                                       | - | 55  | 120 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                                                       | - | 160 | 330 | ns |
| $t_f$        | Turn-Off Fall Time  |                                                                                                       | - | 35  | 80  | ns |

### Drain-Source Diode Characteristics

|                 |                                                          |                                                                               |   |     |     |    |
|-----------------|----------------------------------------------------------|-------------------------------------------------------------------------------|---|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |                                                                               | - | -   | 46  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain to Source Diode Forward Current     |                                                                               | - | -   | 138 | A  |
| V <sub>SD</sub> | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 46 A                                 | - | -   | 1.2 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 46 A, di <sub>F</sub> /dt = 100 A/μs | - | 800 | -   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  |                                                                               | - | 32  | -   | μC |

#### Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2.  $I_{AS} = 9.2\text{ A}, V_{DD} = 50\text{ V}, R_g = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 46\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

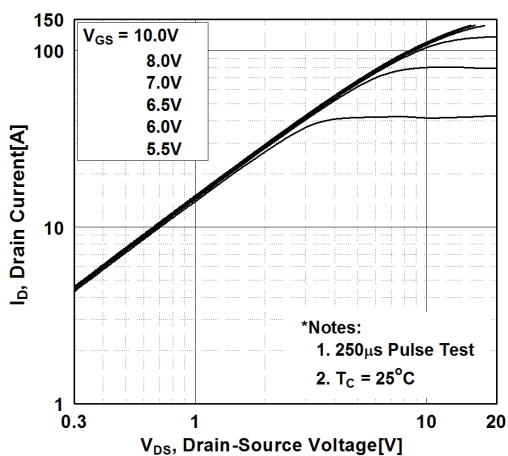


Figure 2. Transfer Characteristics

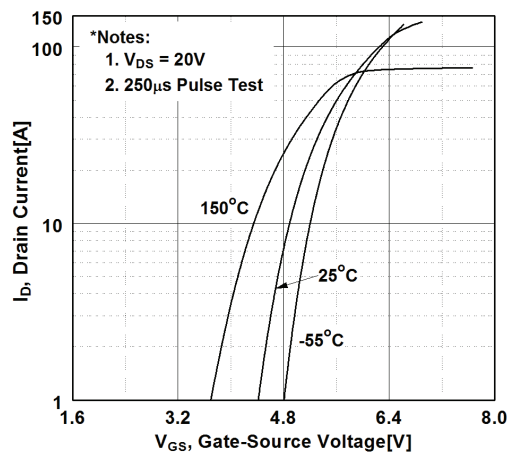


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

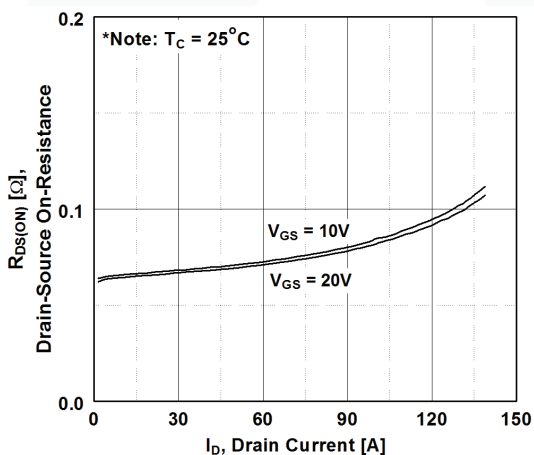


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

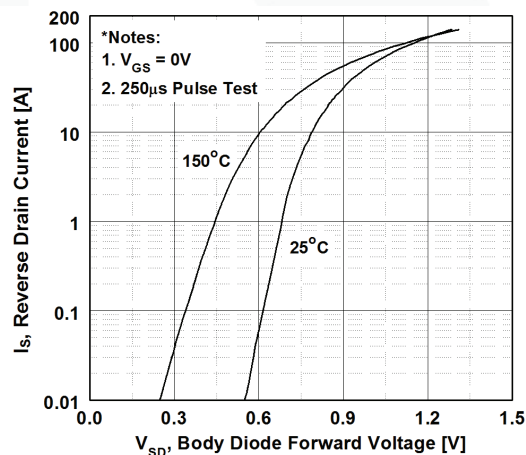


Figure 5. Capacitance Characteristics

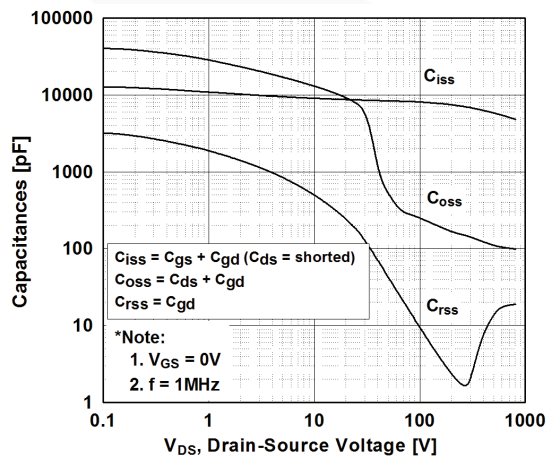
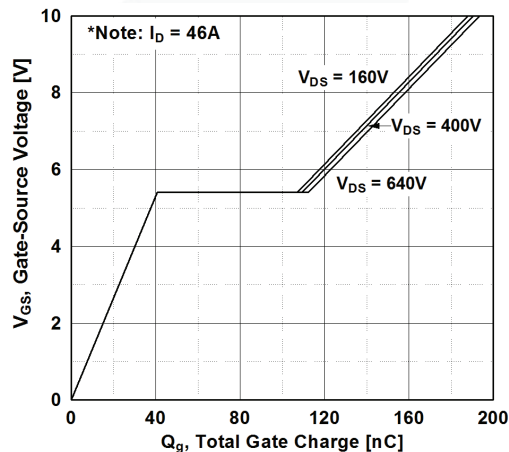
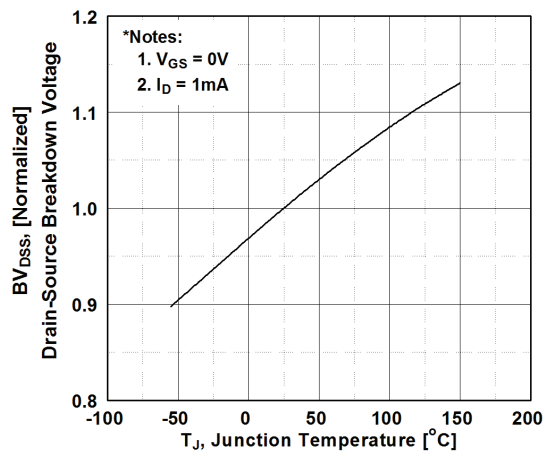


Figure 6. Gate Charge Characteristics

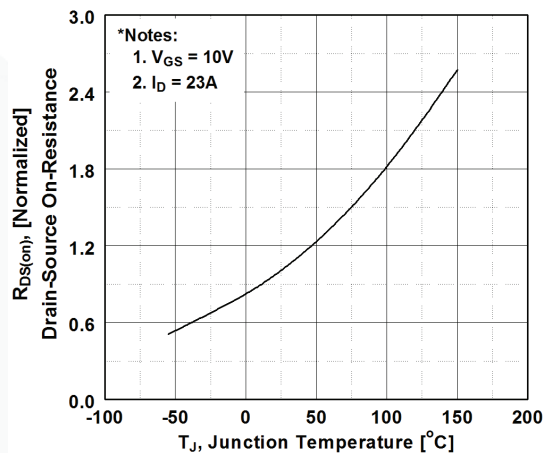


## Typical Performance Characteristics (Continued)

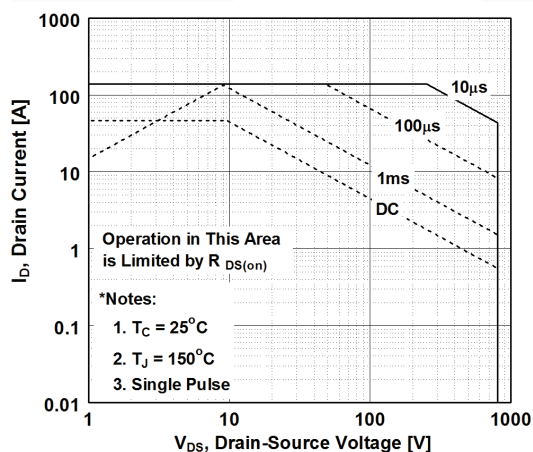
**Figure 7. Breakdown Voltage Variation vs. Temperature**



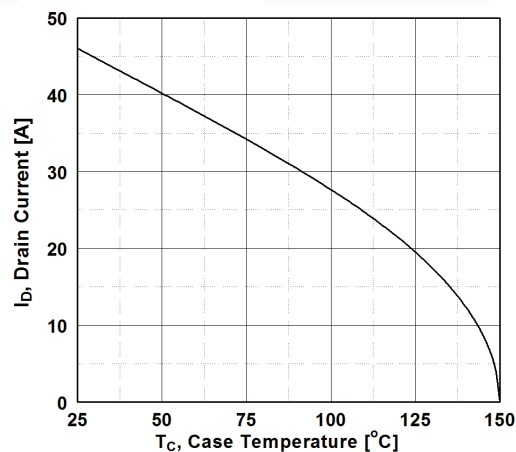
**Figure 8. On-Resistance Variation vs. Temperature**



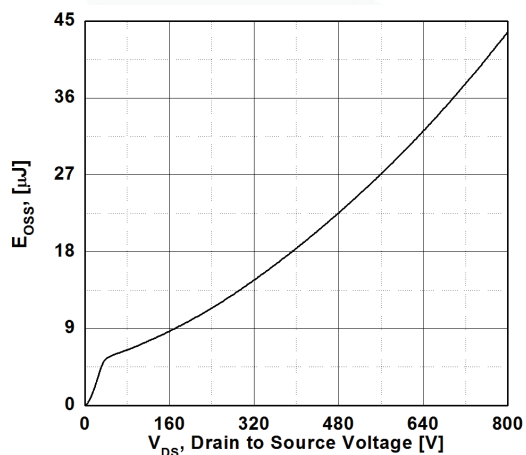
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Eoss vs. Drain to Source Voltage**



## Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

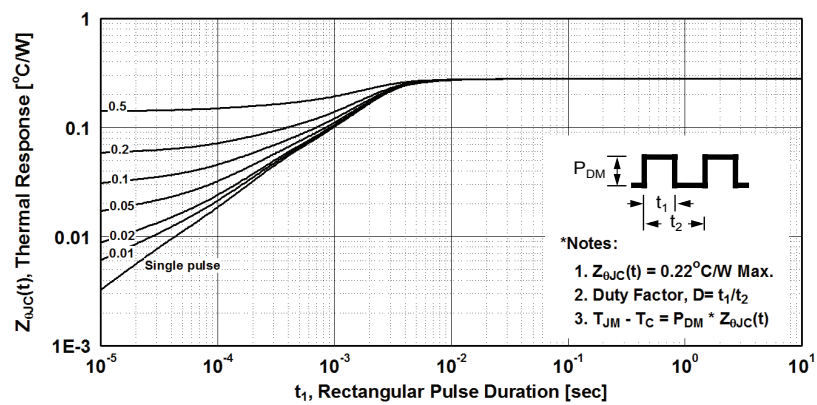


Figure 13. Gate Charge Test Circuit & Waveform

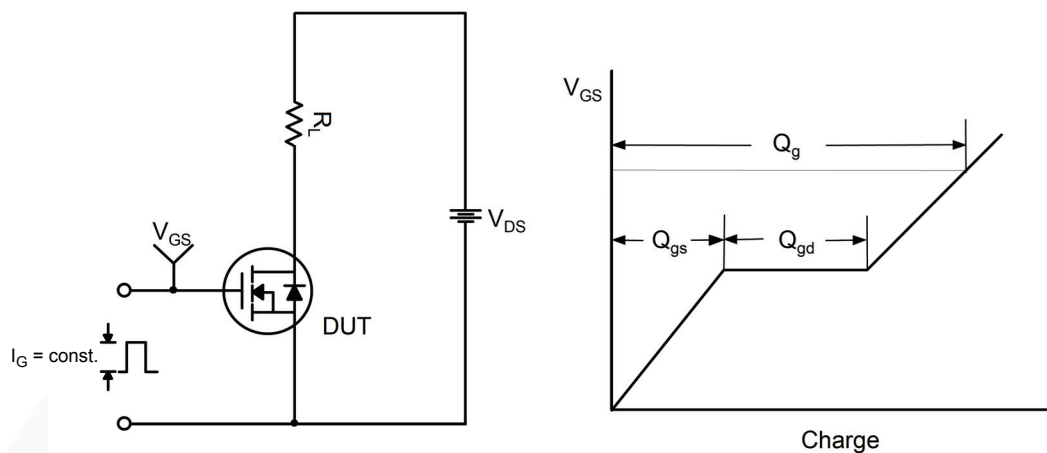


Figure 14. Resistive Switching Test Circuit & Waveforms

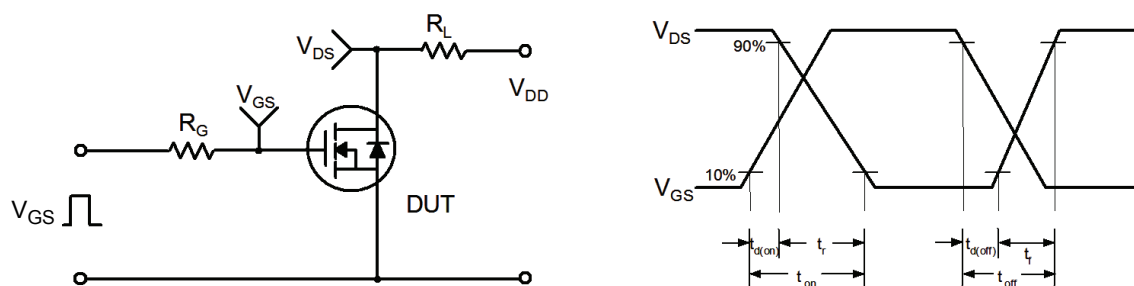


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

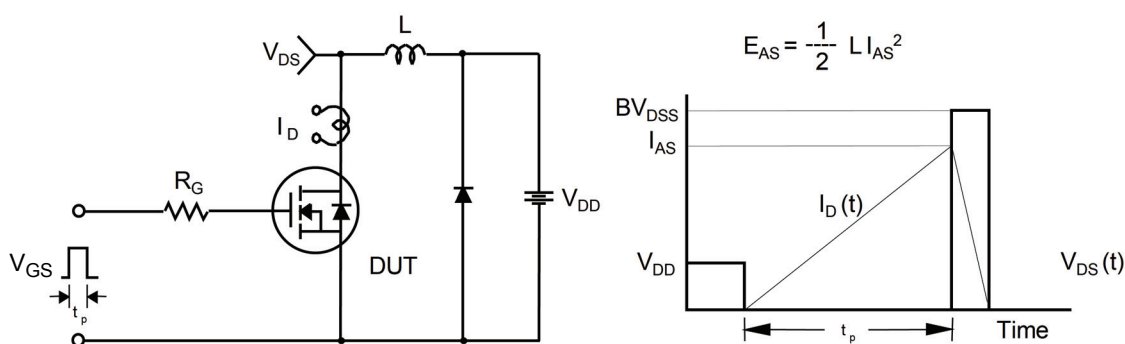
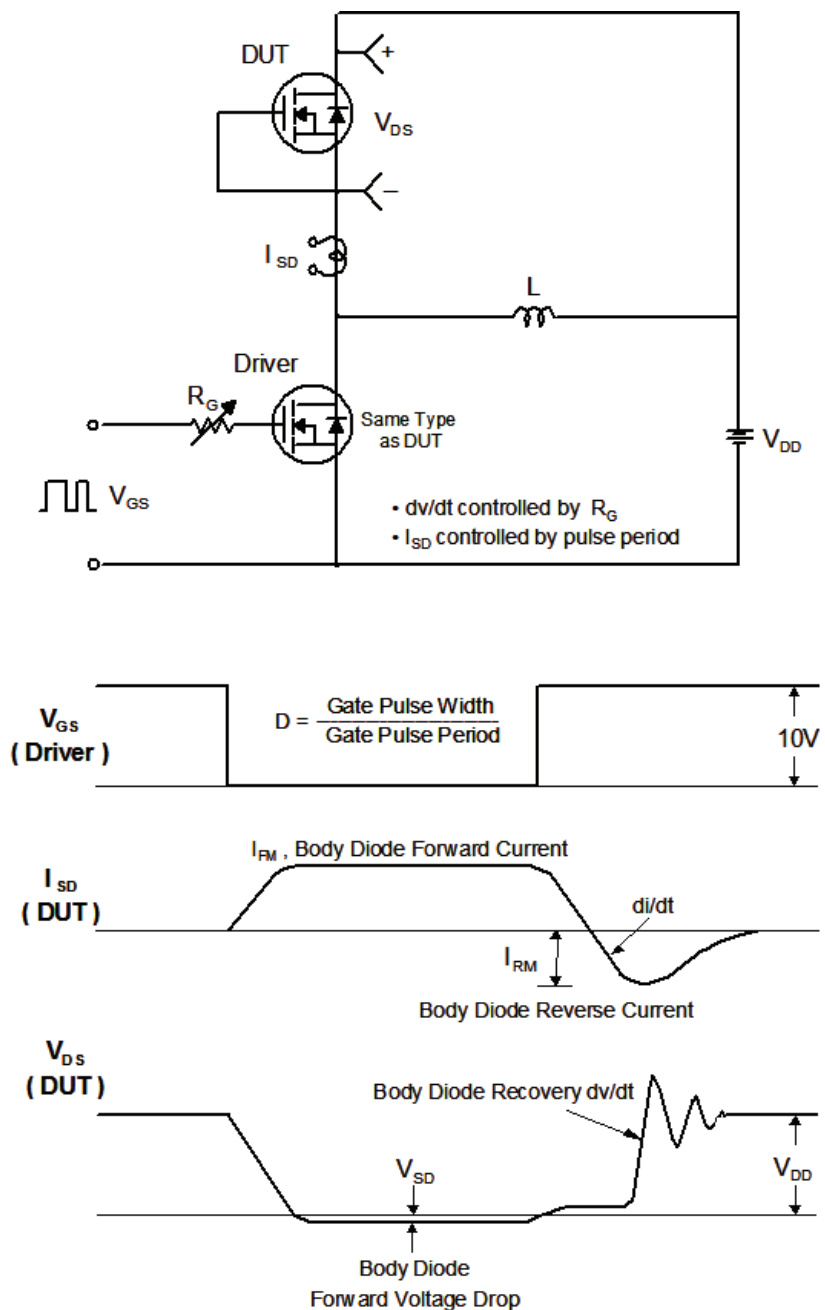
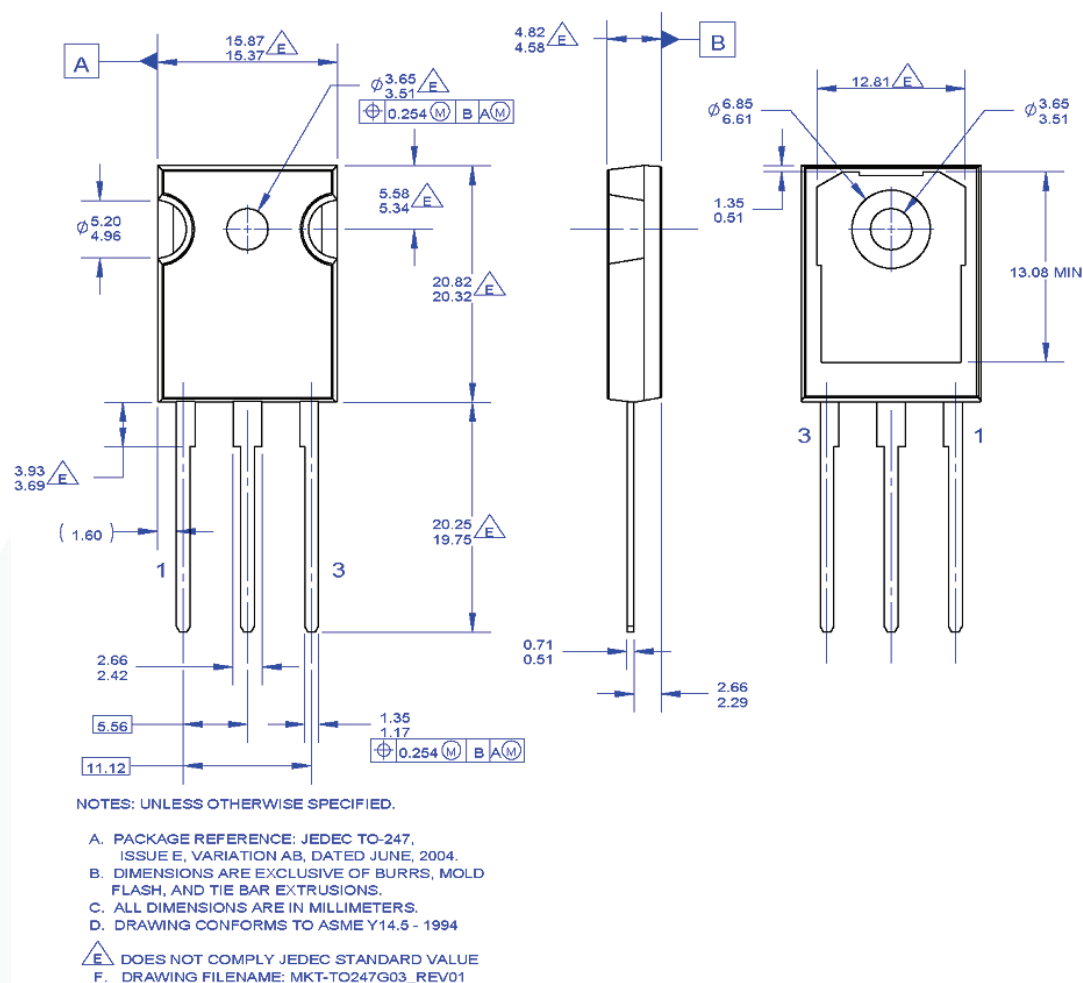


Figure 16. Peak Diode Recovery dv/dt Test Circuit &amp; Waveforms



## Physical Dimensions



**Figure 17. TO-247, MOLDED, 3 LEAD, JEDEC AB LONG LEADS (Active)**

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